

IRFR420APbF IRFU420APbF

HEXFET® Power MOSFET

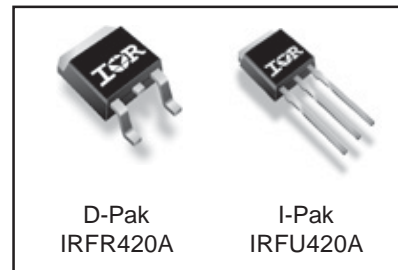
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High speed power switching
- Lead-Free

V _{DSS}	R _{DS(on)} max	I _D
500V	3.0Ω	3.3A

Benefits

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{OSS} specified (See AN 1001)



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	3.3	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	2.1	
I _{DM}	Pulsed Drain Current ①	10	
P _D @ T _C = 25°C	Power Dissipation	83	W
	Linear Derating Factor	0.67	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	3.4	V/ns
T _J	Operating Junction and	-55 to + 150	
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I _{AR}	Avalanche Current④	—	2.5	A
E _{AR}	Repetitive Avalanche Energy④	—	5.0	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.5	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

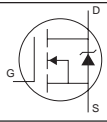
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	500	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	3.0	Ω	V _{GS} = 10V, I _D = 1.5A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.5	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 500V, V _{GS} = 0V
		—	—	250		V _{DS} = 400V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	1.4	—	—	S	V _{DS} = 50V, I _D = 1.5A
Q _g	Total Gate Charge	—	—	17	nC	I _D = 2.5A
Q _{gs}	Gate-to-Source Charge	—	—	4.3		V _{DS} = 400V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	8.5		V _{GS} = 10V, See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time	—	8.1	—	ns	V _{DD} = 250V
t _r	Rise Time	—	12	—		I _D = 2.5A
t _{d(off)}	Turn-Off Delay Time	—	16	—		R _G = 21Ω
t _f	Fall Time	—	13	—		R _D = 97Ω, See Fig. 10 ④
C _{iss}	Input Capacitance	—	340	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	53	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	2.7	—		f = 1.0MHz, See Fig. 5
C _{oss}	Output Capacitance	—	490	—		V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz
C _{oss}	Output Capacitance	—	15	—		V _{GS} = 0V, V _{DS} = 400V, f = 1.0MHz
C _{oss eff.}	Effective Output Capacitance	—	28	—		V _{GS} = 0V, V _{DS} = 0V to 400V ⑤

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	10		
V _{SD}	Diode Forward Voltage	—	—	1.6	V	T _J = 25°C, I _S = 2.5A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	330	500	ns	T _J = 25°C, I _F = 2.5A
Q _{rr}	Reverse Recovery Charge	—	760	1140	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 45mH
R_G = 25Ω, I_{AS} = 2.5A. (See Figure 12)

③ I_{SD} ≤ 2.5A, di/dt ≤ 270A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ C_{oss eff.} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

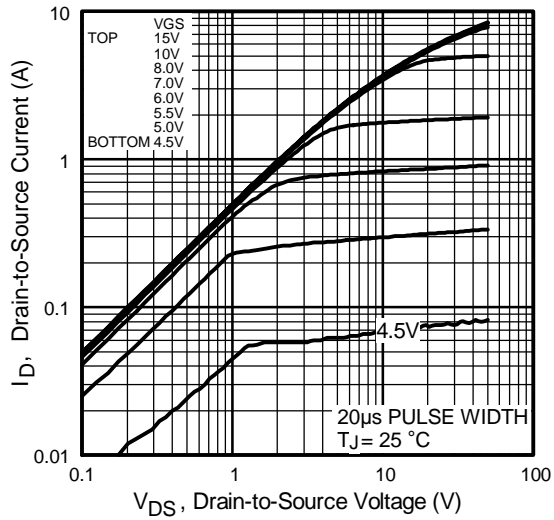


Fig 1. Typical Output Characteristics

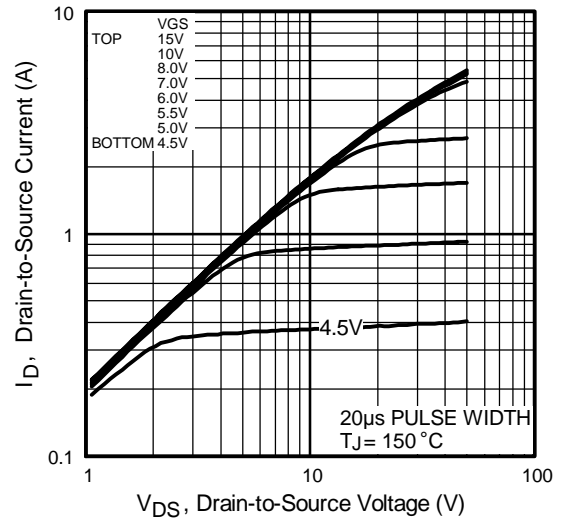


Fig 2. Typical Output Characteristics

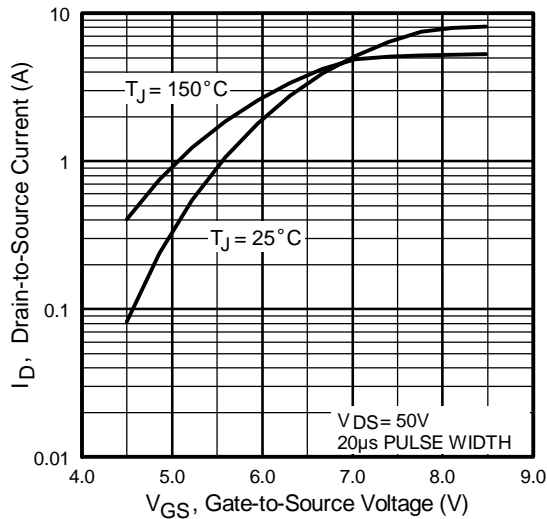


Fig 3. Typical Transfer Characteristics

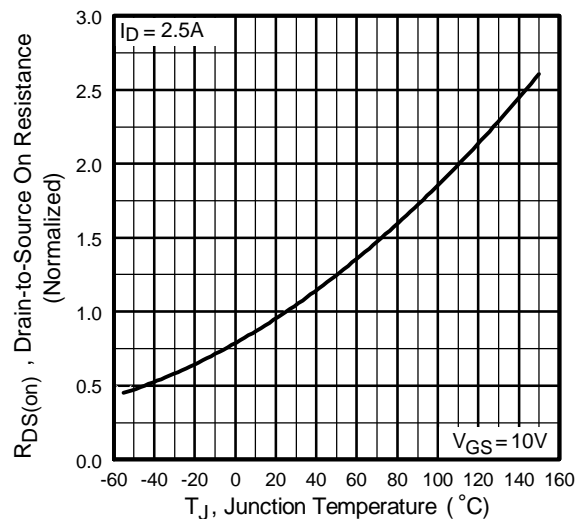


Fig 4. Normalized On-Resistance Vs. Temperature

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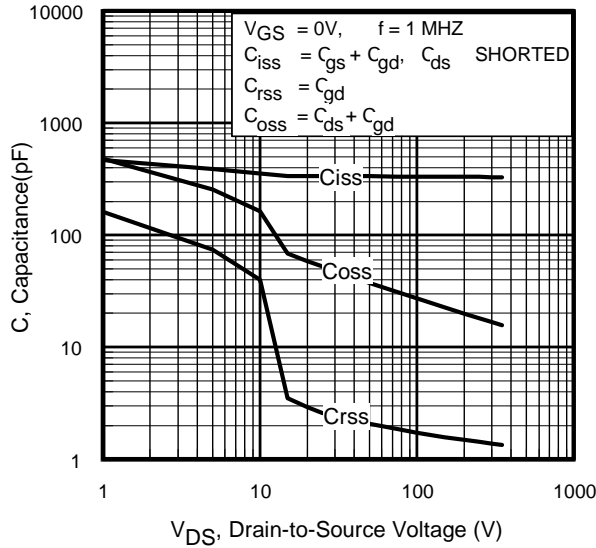


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

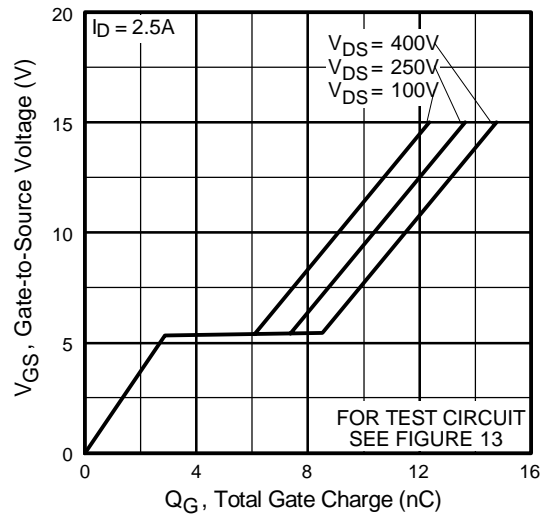


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

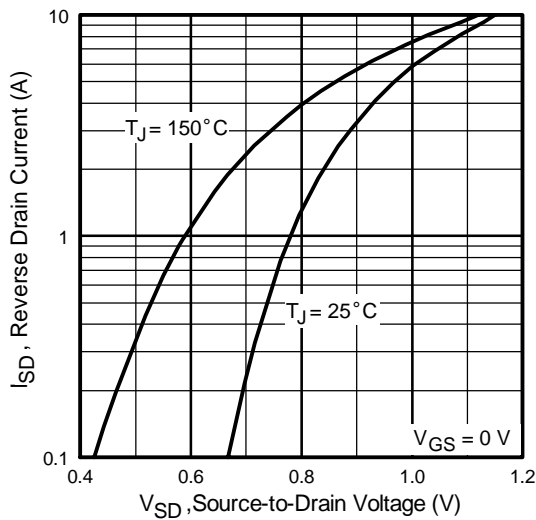


Fig 7. Typical Source-Drain Diode Forward Voltage

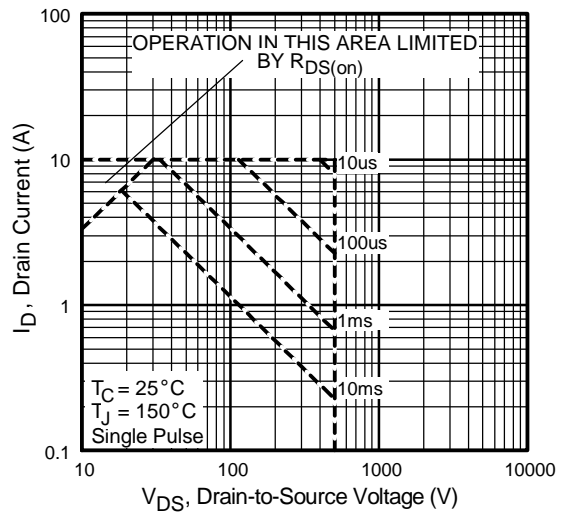


Fig 8. Maximum Safe Operating Area

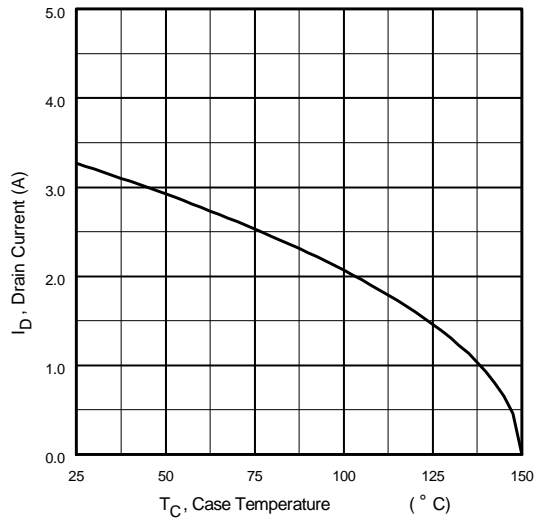


Fig 9. Maximum Drain Current Vs. Case Temperature

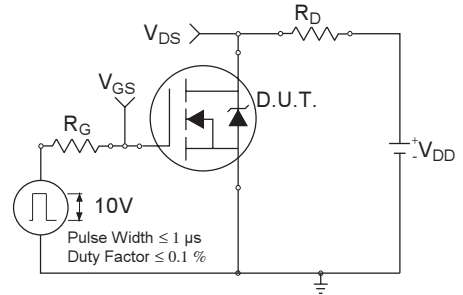


Fig 10a. Switching Time Test Circuit

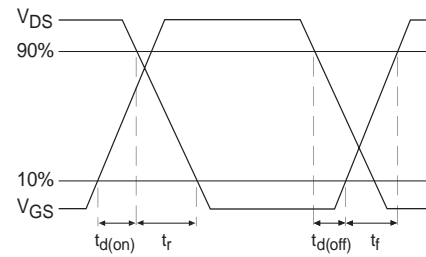


Fig 10b. Switching Time Waveforms

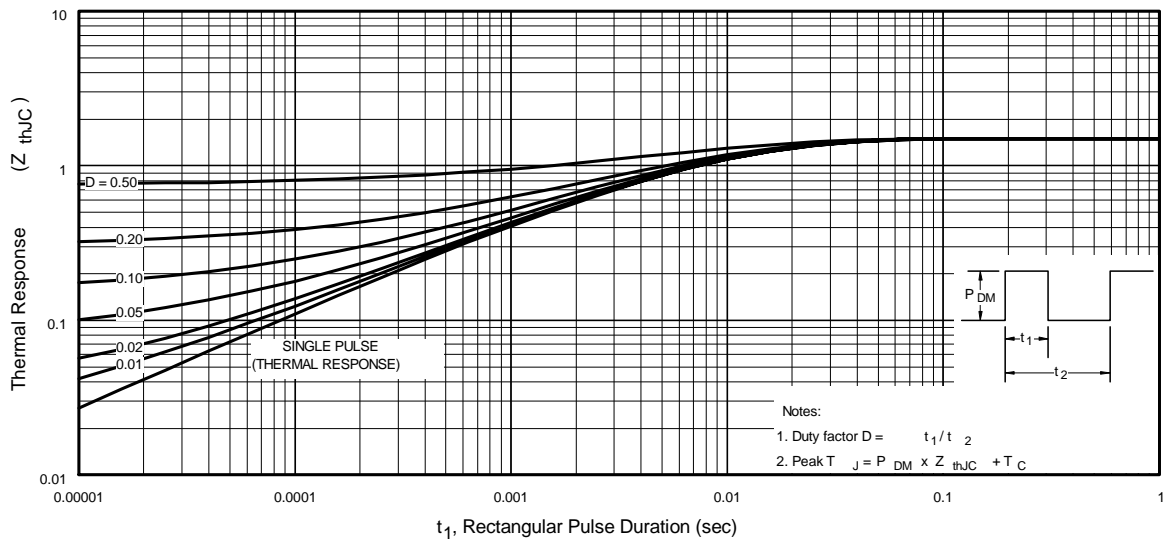


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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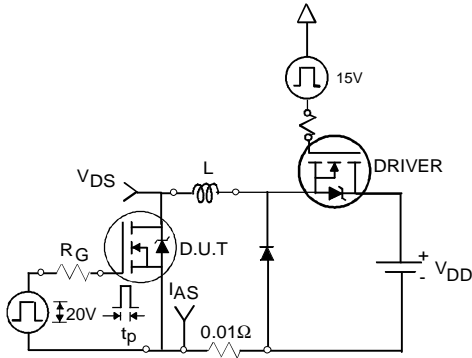


Fig 12a. Unclamped Inductive Test Circuit

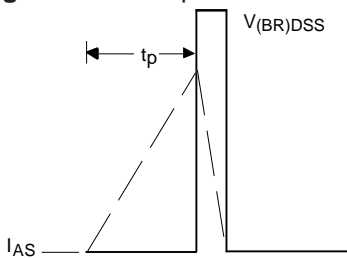


Fig 12b. Unclamped Inductive Waveforms

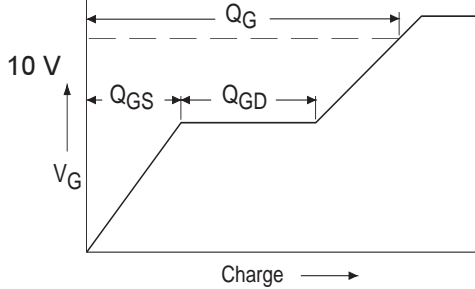


Fig 13a. Basic Gate Charge Waveform

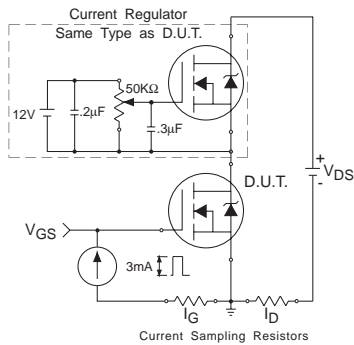


Fig 13b. Gate Charge Test Circuit

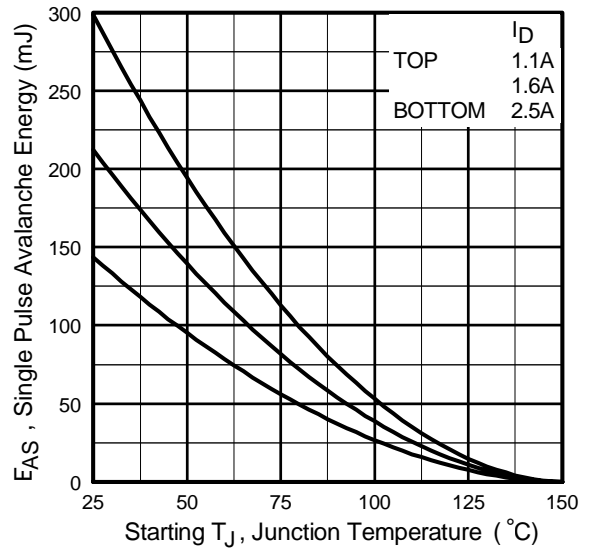


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

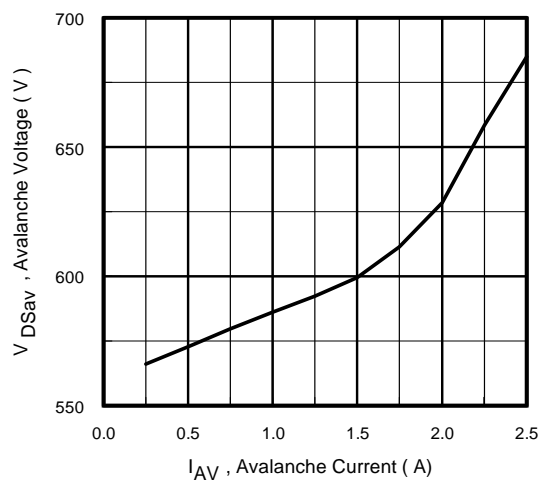
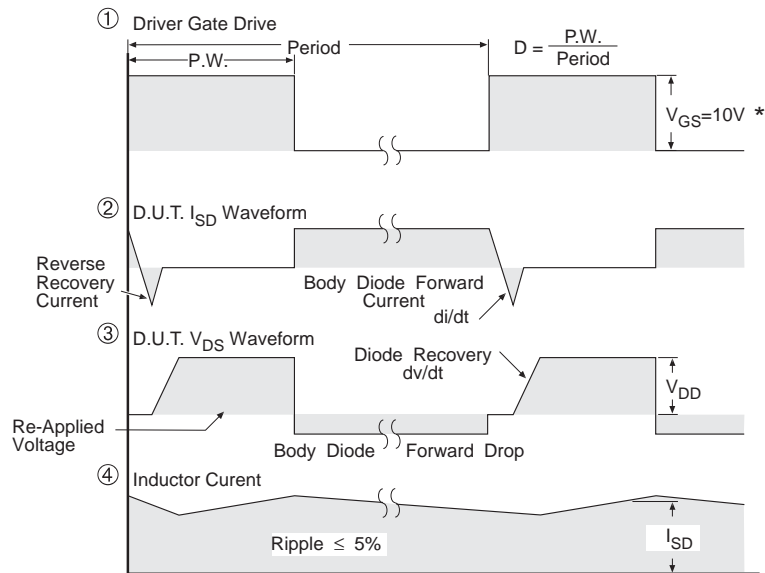
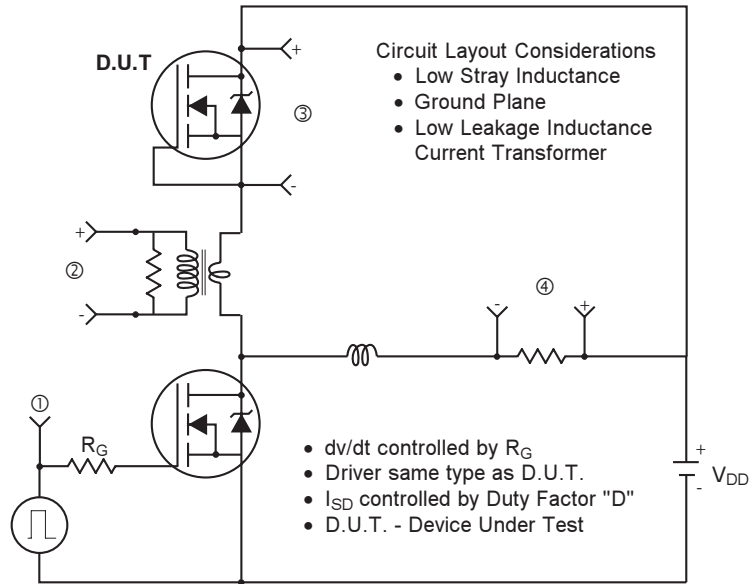


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

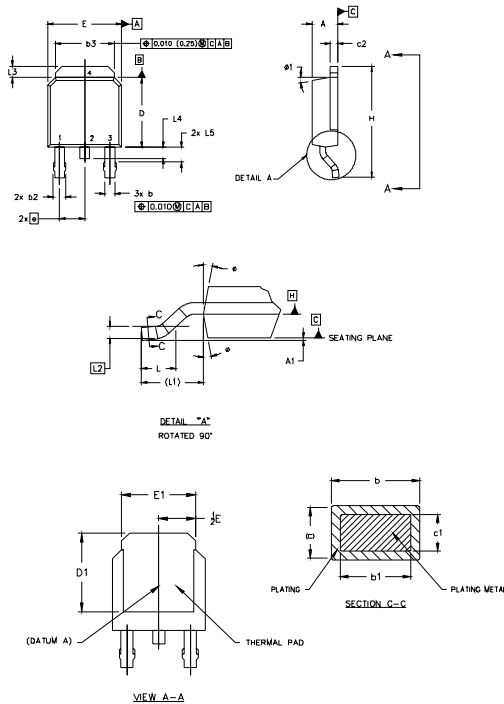
Fig 14. For N-Channel HEXFET® Power MOSFETs

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D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	8.40	10.41	.370	.410	
L	1.40	1.76	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.025 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

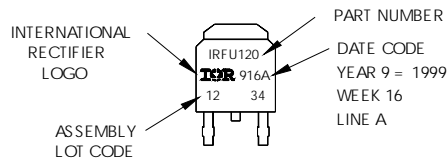
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

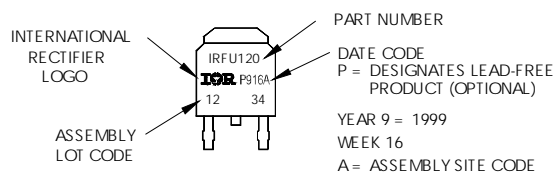
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120 WITH ASSEMBLY LOT CODE 1234 ASSEMBLED ON VVV 16, 1999 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"

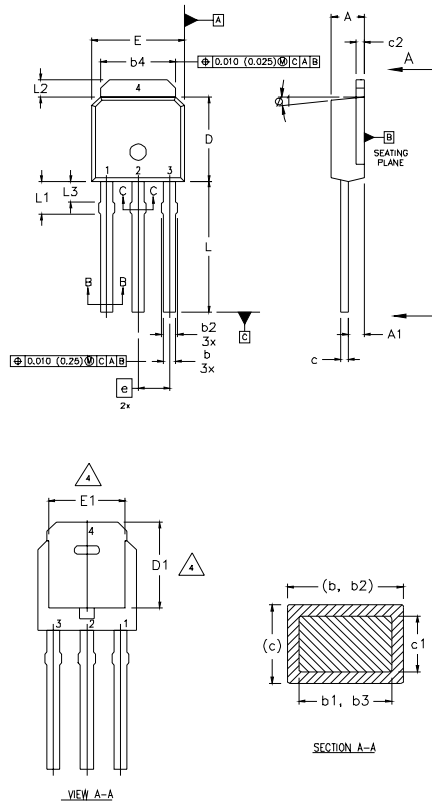


OR



I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
 - 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 - 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
 - 5 LEAD DIMENSION UNCONTROLLED IN L3.
 - 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
 - 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
 - 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

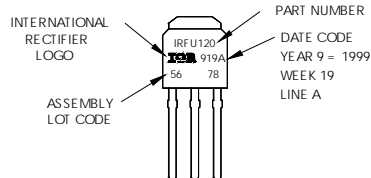
HEXFEEET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

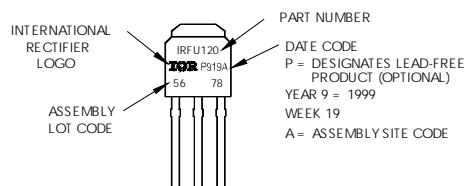
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
e1	0"	15"	0"	15"	

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW19, 1999 IN THE ASSEMBLY LINE "A"
Note: "P" in assembly line position indicates "Lead-Free"



OR

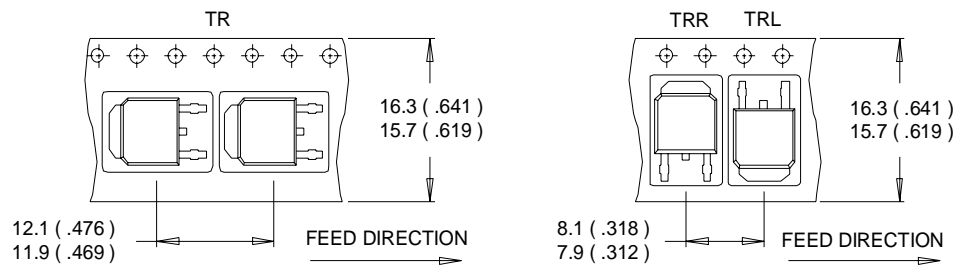


IRFR/U420APbF

International
IR Rectifier

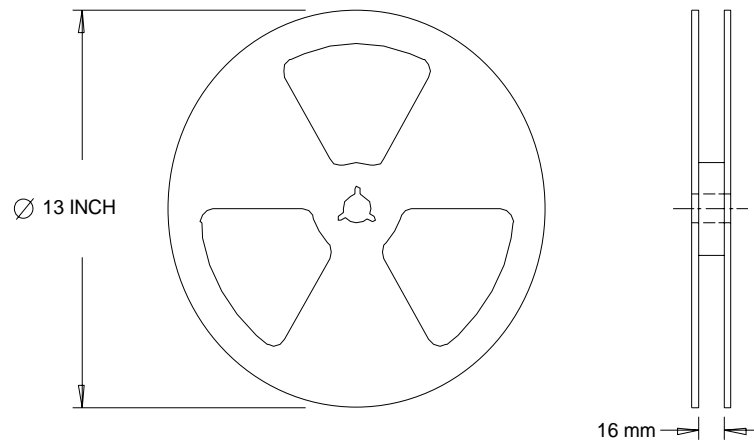
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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